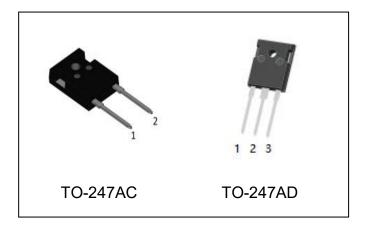






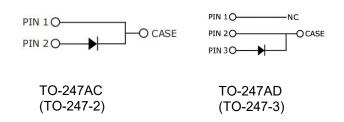
## S3D40065H2/S3D40065D1 650V SIC POWER SCHOTTKY RECTIFIERS



#### **Description**

This 650V 40A diode is high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S3D40065H2/S3D40065D1 is ideal for energy sensitive, high frequency applications in challenging environments.

### **Circuit Diagram**



### **Features**

- 175°C T<sub>J</sub> operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- "-A" is an AEC-Q101 qualified device
- Terminals finish: 100% Pure Tin
- Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

### **Applications**

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- · Switching supply output rectification
- Reverse polarity protection







## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>DC</sub>	-	650	V
	I <sub>F (AV)1</sub>	Tc=25°C	128	Α
Average Rectified Forward Current	I <sub>F (AV)2</sub>	Tc=135°C	58	Α
	I <sub>F (AV)3</sub>	Tc=152°C	40	Α
Repetitive Peak Forward Surge Current	I <sub>FRM1</sub>	10ms, Half Sine pulse, T <sub>C</sub> =25°C	190	Α
Trepetitive Fear Forward Surge Surrent	I <sub>FRM2</sub>	10ms, Half Sine pulse, T <sub>C</sub> =110°C	120	Α
Book One Civele New Bornetitive Course Course	I <sub>FSM1</sub>	10ms, Half Sine pulse, T <sub>C</sub> =25°C	320	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM2</sub>	10ms, Half Sine pulse, T <sub>C</sub> =110°C	270	А
Dower Discipation	P <sub>tot1</sub>	T <sub>C</sub> =25°C	441	W
Power Dissipation	P <sub>tot2</sub>	T <sub>C</sub> =110°C	191	W

## **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	$V_{F1}$	@ 40A, Pulse, T <sub>J</sub> = 25 °C	1.45	1.7	V
	V <sub>F2</sub>	@ 40A, Pulse, T <sub>J</sub> = 175 °C	1.65	2.0	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	3	50	uA
	I <sub>R2</sub>	$@V_R = \text{rated } V_{R,} T_J = 175 ^{\circ}\text{C}$	30	200	uA
Junction Capacitance	Ст	V <sub>R</sub> =0V, T <sub>J</sub> =25℃, f=1MHz	3100	-	pF
Reverse Recovery Charge	Qc	$I_F$ = 40A, di/dt=200A/ $\mu$ s VR = 400 V, T <sub>J</sub> =25°C	193.4	-	nC
Capacitance Stored Energy	Ec	V <sub>R</sub> = 400 V, T <sub>J</sub> =25°C	47.3	-	μJ

 $<sup>^*</sup>$  Pulse width < 300  $\mu$ s, duty cycle < 2%

# Thermal-Mechanical Specifications:

Characteristics	Symbol	S3D40065H2	S3D40065D1	Units
Junction Temperature	TJ	-55 to +175	-55 to +175	ů
Storage Temperature	T <sub>stg</sub>	-55 to +175	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R <sub>θ</sub> JC	0.42	0.38(per leg)	°C/W

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com sales@ smc-diodes.com •



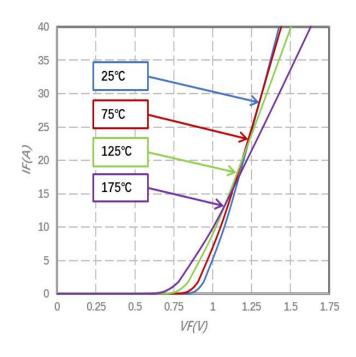




## **Ordering Information**

Device	Package	Plating	Shipping
S3D40065H2	TO-247AC(TO-247-2)	Pure Sn	25pcs / tube
S3D40065D1	TO-247AD(TO-247-3)	Pure Sn	25pcs / tube

### **Ratings and Characteristics Curves**



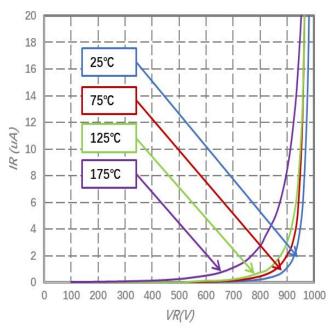


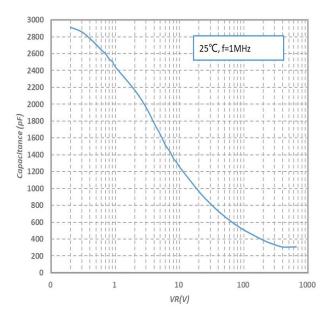
Fig.1-Typical Forward Voltage Characteristics

Fig.2-Typical Reverse Characteristics









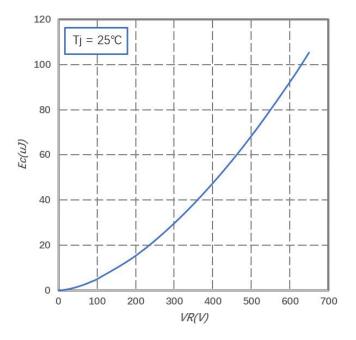
250
200
200
150
100
50
100
200
300
400
500
600
700
VR(V)

300

Tj = 25°C

Fig.3-Capacitance vs. Reverse Voltage

Fig.4-Total Capacitance Charge vs. Reverse Voltage



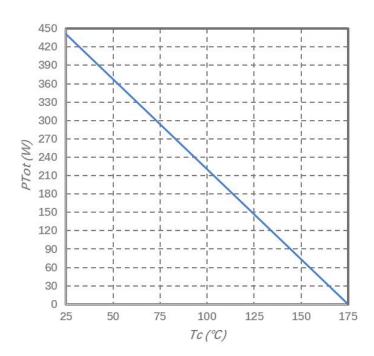


Fig.5-Capacitance Stored Energy

Fig.6-Power Derating

<sup>•</sup> China - Germany - Korea - Singapore - United States •

<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •







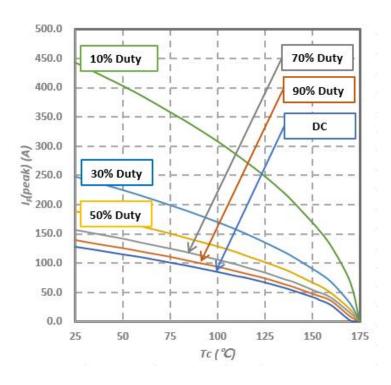
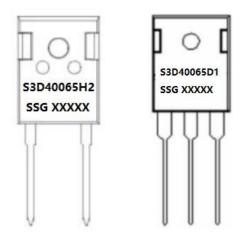


Fig.7-Current Derating

## **Marking Diagram**



Where XXXXX is YYWWL

 S3D
 = Device Type

 H2/D1
 = Package type

 40
 = Forward Current (40A)

 065
 = Reverse Voltage (650V)

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

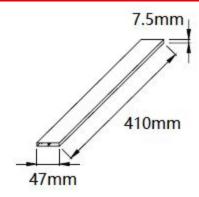
Epoxy resin UL:94V-0





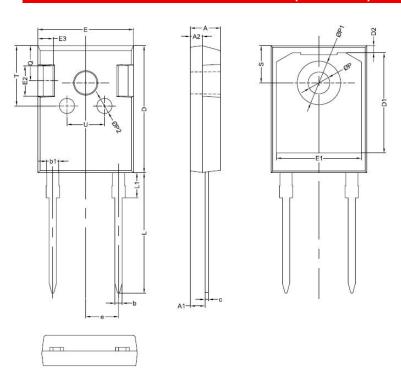


## **Tube Specification**



(TO-247-2/TO-247-3)

## **Mechanical Dimensions TO-247AC(TO-247-2)**



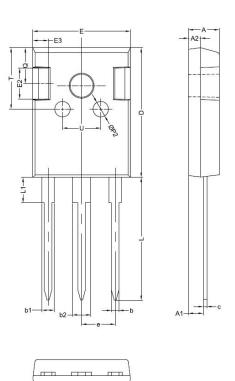
SYMBOL	Millimeters				
	MIN.	TYP.	MAX.		
Α	4.80	5.00	5.20		
A1	2.20	2.41	2.61		
A2	1.90	2.00	2.10		
b	1.10	1.20	1.35		
b1	1.80	2.00	2.20		
С	0.50	0.60	0.75		
D	20.30	21.00	21.20		
D1		16.58			
D2		1.17			
E	15.60	15.80	16.00		
E1		14.02			
E2		5.00			
E3		2.50			
е		5.44			
L	19.42	19.92	20.42		
L1		4.13			
Р	3.50	3.60	3.70		
P1	7.1	7.19	7.40		
P2		2.50			
Q		5.80			
Q S	6.05	6.15	6.25		
Т		10.00			
U		6.20			

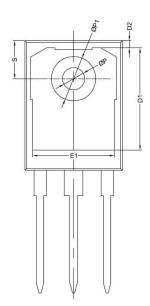






## **Mechanical Dimensions TO-247AD**





SYMBOL	Millimeters				
	MIN.	TYP.	MAX.		
Α	4.80		5.20		
A1	2.00		2.75		
A2	1.90		2.10		
b	1.00		1.40		
b1	1.80		2.40		
b2	2.80		3.40		
С	0.40		0.75		
D	19.80		21.20		
D1		16.55			
D2 E		1.20			
E	15.20		16.00		
E1		13.30			
E2		5.00			
E3		2.50			
е	5.20		5.70		
L	13.90		20.70		
L1	3.70		4.30		
Р	3.50		3.70		
P1	7.1		7.40		
P2		2.50			
P2 Q S		5.80			
S	6.05		6.25		
Т		10.00			
U		6.20			







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